

**Before the first paragraph, please insert:**

This application is a divisional application of U.S. Application Serial No. 09/905,330 filed on July 13, 2001, entitled "Tunneling Magnetoresistive Element And Method Of Manufacturing The Same".

**In the Specification**

Please amend the paragraph on page 16, lines 15-16 as follows:

(Amended) ~~AA~~another method of manufacturing a tunneling magnetoresistive element of the present invention comprises:

Please amend the paragraph on page 16, lines 17-23 as follows:

(Amended) ~~(g)~~(a) the step of forming an electrode layer on a substrate, and then laminating an antiferromagnetic layer, a pinned magnetic layer in which magnetization is pinned in a predetermined direction by an exchange coupling magnetic field with the antiferromagnetic layer, an insulating barrier layer and a free magnetic layer in turn from the bottom to form a multilayer film;

Please amend the paragraph on page 16, lines 24-26 as follows:

(Amended) ~~(h)~~(b) the step of forming, on a sensitive zone of the multilayer film, a lift-off resist layer having notched portions formed on the lower side thereof;

Please amend the paragraph beginning on page 16, line 27 and ending on page 17, line 2 as follows:

(Amended) ~~(i)~~(c) the step of removing both sides of the multilayer film leaving at least a portion of the multilayer film below the resist layer;

Please amend the paragraph on page 17, lines 3-7 as follows:

(Amended) ~~(j)~~(d) the step of forming insulating layers on both sides of the multilayer film so that the multilayer film-side ends of the upper surfaces of the insulating layers are lower than both ends of the upper surface of the free magnetic layer;

Please amend the paragraph on page 17, lines 8-12 as follows:

(Amended) ~~(k)~~(e) the step of forming domain control layers on the insulating layers by sputtering obliquely to the substrate so that the domain control layers contact both ends of the free magnetic layer, and extend on dead zones of the multilayer film; and

Please amend the paragraph on page 17, lines 13-15 as follows:

(Amended) ~~(f)~~(f) the step of removing the resist layer, and forming an electrode layer on the multilayer film and the domain control layers.

Please amend the paragraph on page 17, lines 20-21 as follows:

(Amended) ~~A~~Another method of manufacturing a tunneling magnetoresistive element of the present invention comprises:

Please amend the paragraph beginning on page 17, line 22 and ending on page 18, line 1 as follows:

(Amended) ~~(m)~~(a) the step of forming an electrode layer on a substrate, and then laminating a free magnetic layer, an insulating barrier layer, a pinned magnetic layer, and an antiferromagnetic layer for pinning magnetization of the pinned magnetic layer in a predetermined direction by an exchange coupling magnetic field in turn from the bottom to form a multilayer film;

Please amend the paragraph on page 18, lines 2-4 as follows:

(Amended) ~~(n)~~(b) the step of forming, on the multilayer film, a lift-off resist layer having notched portions formed on the lower side thereof;

Please amend the paragraph on page 18, lines 5-7 as follows:

(Amended) ~~(o)~~(c) the step of removing both sides of the multilayer film leaving a portion of the multilayer film below the resist layer;

Please amend the paragraph on page 18, lines 8-11 as follows:

(Amended) ~~(p)~~(d) the step of forming domain control layers on both sides of the multilayer film so that the multilayer film- side ends contact at least portions of both ends of the free magnetic layer;

Please amend the paragraph on page 18, lines 12-16 as follows:

(Amended) ~~(g)~~(e) the step of forming insulating layers on the domain control layers by sputtering obliquely to the multilayer film so that the multilayer film-side ends of the upper surfaces of the insulating layers coincide with both ends of the upper surface of the multilayer film; and

Please amend the paragraph on page 18, lines 17-19 as follows:

(Amended) ~~(f)~~(f) the step of removing the resist layer, and forming an electrode layer on the multilayer film and the insulating layers.

Please amend the paragraph on page 19, lines 6-7 as follows:

(Amended) ~~A~~Another method of manufacturing a tunneling magnetoresistive element of the present invention comprises:

Please amend the paragraph on page 19, lines 8-14 as follows:

(Amended) ~~(s)~~(a) the step of forming an electrode layer on a substrate, and then laminating a free magnetic layer, an insulating barrier layer, a pinned magnetic layer, and an antiferromagnetic layer for pinning magnetization of the pinned magnetic layer in a predetermined direction by an exchange coupling magnetic field in turn from the bottom to form a multilayer film;

Please amend the paragraph on page 19, lines 15-17 as follows:

(Amended) ~~(t)~~(b) the step of forming, on a sensitive zone of the multilayer film, a lift-off resist layer having notched portions formed on the lower side thereof;

Please amend the paragraph on page 19, lines 18-20 as follows:

(Amended) ~~(u)~~(c) the step of removing both sides of the multilayer film leaving at least a portion of the multilayer film below the resist layer;

Please amend the paragraph on page 19, lines 21-24 as follows:

(Amended) ~~(v)~~(d) the step of forming domain control layers on both sides of the multilayer film so that the multilayer film-side ends contact at least portions of both ends of the free magnetic layer;

Please amend the paragraph beginning on page 19, line 25 and ending on page 20, line 1 as follows:

(Amended) ~~(w)~~(e) the step of forming insulating layers on the domain control layers by sputtering obliquely to the multilayer film so that the insulating layers extend on dead zones of the multilayer film; and

Please amend the paragraph on page 20, lines 2-4 as follows:

(Amended) ~~(\*)~~(f) the step of removing the resist layer, and forming an electrode layer on the multilayer film and the insulating layers.